## 2 A, 1.5 MHz PWM step-down switching regulator with synchronous rectification

## Features

- 1.5 MHz fixed frequency PWM with current control mode
- 2 A output current capability
- Typical efficiency: > $90 \%$
- $2 \%$ DC output voltage tolerance
- Two versions available: power good or inhibit
- Integrated output over-voltage protection
- Non switching quiescent current: (typ) 1.5 mA over temperature range
- $\mathrm{R}_{\text {DSON }}(\mathrm{typ}) 100 \mathrm{~m} \Omega$
- Utilizes tiny capacitors and inductors
- Operating junction temp. $-30^{\circ} \mathrm{C}$ to $125^{\circ} \mathrm{C}$
- Available in DFN6 ( $3 \times 3 \mathrm{~mm}$ ) exposed pad


## Description

The ST1S09 is a step-down DC-DC converter optimized for powering low output voltage applications. It supplies a current in excess of 2 A over an input voltage range from 2.7 V to 6 V .
A high PWM switching frequency ( 1.5 MHz ) allows the use of tiny surface-mount components.


Moreover, since the required synchronous rectifier is integrated, the number of the external components is reduced to minimum: a resistor divider, an inductor and two capacitors. The Power Good function continuously monitors the output voltage. An open drain Power Good flag is released when the output voltage is within regulation. In addition, a low output ripple is guaranteed by the current mode PWM topology and by the use of low ESR SMD ceramic capacitors. The device is thermally protected and the output current limited to prevent damages due to accidental short circuit. The ST1S09 is available in the DFN6 ( $3 \times 3 \mathrm{~mm}$ ) package.

Table 1. Device summary

| Order codes | Package |
| :---: | :---: |
| ST1S09PUR | DFN6D $(3 \times 3 \mathrm{~mm})$ |
| ST1S09APUR $^{(1)}$ | DFN6D $(3 \times 3 \mathrm{~mm})$ |
| ST1S09IPUR | DFN6D $(3 \times 3 \mathrm{~mm})$ |

[^0]
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## 1 <br> Diagram

Figure 1. Schematic diagram

(*) Only for ST1S09IPU
(**) Only for ST1S09PU

## 2 Pin configuration

Figure 2. Pin connections (top view)


Table 2. Pin description

| Pin $\mathbf{n}^{\circ}$ | Symbol | Name and function |
| :---: | :---: | :--- |
| 1 | FB | Feedback voltage |
| 2 | GND | System ground |
| 3 | SW | Switching pin |
| 4 | $\mathrm{~V}_{\text {IN_SW }}$ | Power supply for the MOSFET switch |
| 5 | $\mathrm{~V}_{\text {IN_A }}$ | Power supply for analog circuit |
| 6 | INH/PG/NC | Inhibit (to turn off the device) / Power Good / Not Connected |
| Exposed <br> Pad | GND | To be connected to PCB ground plane for optimal electrical and thermal <br> performance |

## 3 Maximum ratings

Table 3. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\text {IN_SW }}$ | Positive power supply voltage | -0.3 to 7 | V |
| $\mathrm{~V}_{\text {IN_A }}$ | Positive power supply voltage | -0.3 to 7 | V |
| $\mathrm{~V}_{\text {INH }}$ | Inhibit voltage (I version) | -0.3 to $\mathrm{V}_{\mathrm{I}}+0.3$ | V |
| SWITCH Voltage | Max. voltage of output pin | -0.3 to 7 | V |
| $\mathrm{~V}_{\text {FB }}$ | Feedback voltage | -0.3 to 3 | V |
| PG | Power Good open drain | -0.3 to 7 | V |
| $\mathrm{~T}_{\mathrm{J}}$ | Max junction temperature | -40 to 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {STG }}$ | Storage temperature range | -65 to 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {LEAD }}$ | Lead temperature (soldering) 10 sec | 260 | ${ }^{\circ} \mathrm{C}$ |

Note: $\quad$ Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

Table 4. Thermal data

| Symbol | Parameter | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{R}_{\text {thJC }}$ | Thermal resistance junction-case | 10 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{R}_{\text {thJA }}$ | Thermal resistance junction-ambient | 55 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Table 5. ESD performance

| Symbol | Parameter | Test conditions | Value | Unit |
| :---: | :--- | :--- | :---: | :---: |
| ESD | ESD protection voltage | HBM | 2 | kV |
| ESD | ESD protection voltage | MM | 500 | V |

## 4 Electrical characteristics

Refer to Figure 21 application circuit $\mathrm{V}_{\mathrm{IN} \text { SW }}=\mathrm{V}_{\mathrm{IN} \text { _A }}=5 \mathrm{~V}, \mathrm{~V}_{\mathrm{O}}=1.2 \mathrm{~V}, \mathrm{C} 1=4.7 \mu \mathrm{~F}$, $\mathrm{C}_{2}=22 \mu \mathrm{~F}, \mathrm{~L} 1=2.7 \mu \mathrm{H}, \mathrm{T}_{\mathrm{J}}=-30$ to $125^{\circ} \mathrm{C}$ (unless otherwise specified. Typical values are referred to $25^{\circ} \mathrm{C}$ )

Table 6. Electrical characteristics for ST1S09PU

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| FB | Feedback voltage |  | 784 | 800 | 816 | mV |
| $\mathrm{I}_{\text {FB }}$ | $V_{\text {FB }}$ pin bias current |  |  |  | 600 | nA |
| $V_{1}$ | Input voltage | $\mathrm{I}_{\mathrm{O}}=10 \mathrm{~mA}$ to 2 A | 4.5 |  | 5.5 | V |
| UV LO | Under voltage lock out threshold | $V_{1}$ Rising | 3.5 | 3.7 | 3.9 | V |
|  |  | Hysteresis |  | 150 |  | mV |
| OVP | Over voltage protection threshold | $\mathrm{V}_{\mathrm{O}}$ rising | $1.05 \mathrm{~V}_{\mathrm{O}}$ | $1.1 \mathrm{~V}_{\mathrm{O}}$ |  | V |
|  | Over voltage protection hysteresis | $\mathrm{V}_{\mathrm{O}}$ falling |  | 5 |  | \% |
| Iovp | Overvoltage clamping current | $\mathrm{V}_{\mathrm{O}}=1.2 \mathrm{~V}$ |  | 300 |  | mA |
| $\mathrm{I}_{\mathrm{Q}}$ | Quiescent current | Not switching |  | 1.5 | 2.5 | mA |
| 10 | Output current | $\mathrm{V}_{\mathrm{I}}=4.5$ to $5.5 \mathrm{~V}^{(1)}$ | 2 |  |  | A |
| $\% \mathrm{~V}_{\mathrm{O}} / \Delta \mathrm{V}_{\text {I }}$ | Output line regulation | $\mathrm{V}_{\mathrm{I}}=4.5 \mathrm{~V}$ to $5.5 \mathrm{~V}, \mathrm{I}_{\mathrm{O}}=100 \mathrm{~mA}{ }^{(1)}$ |  | 0.16 |  | $\begin{gathered} \% \mathrm{~V}_{\mathrm{O}} \\ \Delta \mathrm{~V}_{\mathrm{l}} \end{gathered}$ |
| $\% \mathrm{~V}_{\mathrm{O}} / \Delta \mathrm{l}_{\mathrm{O}}$ | Output load regulation | $\mathrm{I}_{\mathrm{O}}=10 \mathrm{~mA}$ to $2 \mathrm{~A}^{(1)}$ |  | 0.2 | 0.6 | \% |
| $\mathrm{PWMf}_{S}$ | PWM switching frequency | $\mathrm{V}_{\mathrm{FB}}=0.65 \mathrm{~V}$ | 1.2 | 1.5 | 1.8 | MHz |
| $\mathrm{D}_{\text {MAX }}$ | Maximum duty cycle |  | 80 | 87 |  | \% |
| PG | Power good output threshold |  |  | $0.92 \mathrm{~V}_{\mathrm{O}}$ |  | V |
|  | Power good output voltage low | $\mathrm{I}_{\text {SINK }}=6 \mathrm{~mA}$ open drain output |  |  | 0.4 | V |
| $\mathrm{R}_{\text {DSON }}-\mathrm{N}$ | NMOS switch on resistance | $\mathrm{I}_{\text {SW }}=750 \mathrm{~mA}$ |  | 0.1 |  | $\Omega$ |
| $\mathrm{R}_{\text {DSON }}{ }^{-P}$ | PMOS switch on resistance | $\mathrm{I}_{\text {SW }}=750 \mathrm{~mA}$ |  | 0.1 |  | $\Omega$ |
| $I_{\text {SWL }}$ | Switching current limitation | (1) | 2.5 | 2.9 | 3.5 | A |
| $v$ | Efficiency ${ }^{(1)}$ | $\mathrm{I}_{\mathrm{O}}=10 \mathrm{~mA}$ to $100 \mathrm{~mA}, \mathrm{~V}_{\mathrm{O}}=3.3 \mathrm{~V}$ | 65 |  |  | \% |
|  |  | $\mathrm{I}_{\mathrm{O}}=100 \mathrm{~mA}$ to $2 \mathrm{~A}, \mathrm{~V}_{\mathrm{O}}=3.3 \mathrm{~V}$ | 82 | 87 |  |  |
| TSHDN | Thermal shutdown |  |  | 150 |  | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{HYS}}$ | Thermal shutdown hysteresis |  |  | 20 |  | ${ }^{\circ} \mathrm{C}$ |
| \% $\mathrm{V}_{\mathrm{O}} / \Delta \mathrm{l}_{\mathrm{O}}$ | Load transient response | $\begin{aligned} & \mathrm{I}_{\mathrm{O}}=100 \mathrm{~mA} \text { to } 1 \mathrm{~A}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \\ & \mathrm{t}_{\mathrm{R}}=\mathrm{t}_{\mathrm{F}} \geq 200 \mathrm{~ns}{ }^{(1)} \end{aligned}$ | -10 |  | +10 | \% $\mathrm{V}_{\mathrm{O}}$ |
| \% $\mathrm{V}_{\mathrm{O}} / \Delta \mathrm{l}_{\mathrm{O}}$ | Short circuit removal response | $\begin{aligned} & \mathrm{I}_{\mathrm{O}}=10 \mathrm{~mA} \text { to } \mathrm{I}_{\mathrm{O}}=\text { short }, \\ & \mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \text { (1) } \end{aligned}$ | -10 |  | +10 | \% $\mathrm{V}_{\mathrm{O}}$ |

[^1]Refer to Figure 22 application circuit $\mathrm{V}_{\mathrm{IN} \text { _SW }}=\mathrm{V}_{\mathrm{IN} \text { _A }}=\mathrm{V}_{\text {INH }}=5 \mathrm{~V}, \mathrm{~V}_{\mathrm{O}}=1.2 \mathrm{~V}, \mathrm{C} 1=4.7 \mu \mathrm{~F}$, $\mathrm{C} 2=22 \mu \mathrm{~F}, \mathrm{~L} 1=2.7 \mu \mathrm{H}, \mathrm{T}_{\mathrm{J}}=-30$ to $125^{\circ} \mathrm{C}$ (unless otherwise specified. Typical values are referred to $25^{\circ} \mathrm{C}$ )

Table 7. Electrical characteristics for ST1S09IPU

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| FB | Feedback voltage |  | 784 | 800 | 816 | mV |
| $\mathrm{I}_{\text {FB }}$ | $\mathrm{V}_{\text {FB }}$ pin bias current |  |  |  | 600 | nA |
| $V_{1}$ | Minimum input voltage | $\mathrm{I}_{\mathrm{O}}=10 \mathrm{~mA}$ to 2 A | 2.7 |  |  | V |
| OVP | Over voltage protection threshold | $\mathrm{V}_{\mathrm{O}}$ rising | $1.05 \mathrm{~V}_{\mathrm{O}}$ | $1.1 \mathrm{~V}_{\mathrm{O}}$ |  | V |
|  | Over voltage protection hysteresis | $\mathrm{V}_{\mathrm{O}}$ falling |  | 5 |  | \% |
| $\mathrm{I}_{\mathrm{Q}}$ | Quiescent current | $\mathrm{V}_{\text {INH }}>1.2 \mathrm{~V}$, not switching |  | 1.5 | 2.5 | mA |
|  |  | $\mathrm{V}_{\text {INH }}<0.4 \mathrm{~V}, \mathrm{~T}=-30^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ |  |  | 1 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{0}$ | Output current | $\mathrm{V}_{\mathrm{I}}=2.7$ to $5.5 \mathrm{~V}^{(1)}$ | 2 |  |  | A |
| $\mathrm{V}_{\text {INH }}$ | Inhibit threshold | Device ON, $\mathrm{V}_{\mathrm{I}}=2.7$ to 5.5 V | 1.3 |  |  | V |
|  |  | Device ON, $\mathrm{V}_{\mathrm{I}}=2.7$ to 5 V | 1.2 |  |  |  |
|  |  | Device OFF |  |  | 0.4 |  |
| $\mathrm{I}_{\text {INH }}$ | Inhibit pin current |  |  |  | 2 | $\mu \mathrm{A}$ |
| $\% \mathrm{~V}_{\mathrm{O}} / \Delta \mathrm{V}_{\mathrm{I}}$ | Output line regulation | $\mathrm{V}_{\mathrm{I}}=2.7 \mathrm{~V}$ to $5.5 \mathrm{~V}, \mathrm{I}_{\mathrm{O}}=100 \mathrm{~mA}{ }^{(1)}$ |  | 0.16 |  | $\begin{gathered} \% \mathrm{~V}_{\mathrm{O}} / \\ \Delta \mathrm{V}_{\mathrm{l}} \end{gathered}$ |
| \% $\mathrm{V}_{\mathrm{O}} / \Delta \mathrm{l}_{\mathrm{O}}$ | Output load regulation | $\mathrm{I}_{\mathrm{O}}=10 \mathrm{~mA}$ to $2 \mathrm{~A}^{(1)}$ |  | 0.2 | 0.6 | $\begin{gathered} \% \mathrm{~V}_{\mathrm{O}} \\ \Delta \mathrm{I}_{\mathrm{O}} \end{gathered}$ |
| $\mathrm{PWMf}_{S}$ | PWM switching frequency | $\mathrm{V}_{\mathrm{FB}}=0.65 \mathrm{~V}$ | 1.2 | 1.5 | 1.8 | MHz |
| $\mathrm{D}_{\text {MAX }}$ | Maximum duty cycle |  | 80 | 87 |  | \% |
| $\mathrm{R}_{\text {DSON }}{ }^{-N}$ | NMOS switch on resistance | $\mathrm{I}_{\text {SW }}=750 \mathrm{~mA}$ |  | 0.1 |  | $\Omega$ |
| $\mathrm{R}_{\text {DSON }}{ }^{-P}$ | PMOS switch on resistance | $\mathrm{I}_{\text {SW }}=750 \mathrm{~mA}$ |  | 0.1 |  | $\Omega$ |
| ISWL | Switching current limitation | (1) | 2.5 | 2.9 | 3.5 | A |
| $v$ | Efficiency ${ }^{(1)}$ | $\mathrm{I}_{\mathrm{O}}=10 \mathrm{~mA}$ to $100 \mathrm{~mA}, \mathrm{~V}_{\mathrm{O}}=3.3 \mathrm{~V}$ | 65 |  |  | \% |
|  |  | $\mathrm{I}_{\mathrm{O}}=100 \mathrm{~mA}$ to $2 \mathrm{~A}, \mathrm{~V}_{\mathrm{O}}=3.3 \mathrm{~V}$ | 82 | 87 |  |  |
| $\mathrm{T}_{\text {SHDN }}$ | Thermal shutdown |  |  | 150 |  | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{HYS}}$ | Thermal shutdown hysteresis |  |  | 20 |  | ${ }^{\circ} \mathrm{C}$ |
| \% $\mathrm{V}_{\mathrm{O}} / \Delta \mathrm{l}_{\mathrm{O}}$ | Load transient response | $\begin{aligned} & \mathrm{I}_{\mathrm{O}}=100 \mathrm{~mA} \text { to } 1 \mathrm{~A}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \\ & \mathrm{t}_{\mathrm{R}}=\mathrm{t}_{\mathrm{F}} \geq 200 \mathrm{~ns}{ }^{(1)} \end{aligned}$ | -10 |  | +10 | \% $\mathrm{V}_{\mathrm{O}}$ |
| \% $\mathrm{V}_{\mathrm{O}} / \Delta \mathrm{l}_{\mathrm{O}}$ | Short circuit removal response | $\begin{aligned} & \mathrm{I}_{\mathrm{O}}=10 \mathrm{~mA} \text { to } \mathrm{I}_{\mathrm{O}}=\text { short }, \\ & \mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}{ }^{(1)} \end{aligned}$ | -10 |  | +10 | \% $\mathrm{V}_{\mathrm{O}}$ |

1. Guaranteed by design, but not tested in production.

## $5 \quad$ Typical performance characteristics

$\mathrm{L}=3.3 \mu \mathrm{H}, \mathrm{C}_{\mathrm{I}}=4.7 \mu \mathrm{~F}, \mathrm{C}_{\mathrm{O}}=22 \mu \mathrm{~F}$, unless otherwise specified.

Figure 3. Voltage feedback vs. temperature
Figure 4. Feedback pin bias current vs. temp.


Figure 5. Quiescent current non switching Figure 6. Inhibit voltage vs. temperature vs. temperature


Figure 7. Inhibit voltage vs. input voltage

Figure 8. Output voltage vs. input voltage


Figure 9. Line regulation vs. temperature
Figure 10. Load regulation vs. temperature


Figure 11. PWM Switching frequency vs. temperature


Figure 12. Maximum duty cycle vs. temperature


Figure 13. Under voltage lock out threshold vs. temperature

Figure 14. Efficiency vs. output current



Figure 15. Efficiency vs. temperature


Figure 16. Over voltage protection vs. temperature

Figure 17. Over voltage protection vs. temperature


Figure 18. Over voltage protection hyst. vs. temperature

Figure 19. Load transient

$\mathrm{V}_{\mathrm{I}}=5 \mathrm{~V}, \mathrm{~V}_{\mathrm{O}}=1.2 \mathrm{~V}, \mathrm{I}_{\mathrm{O}}=100 \mathrm{~mA}$ to $\mathrm{A}, \mathrm{L}=3.3 \mu \mathrm{H}$,
$\mathrm{C}_{\mathrm{I}}=4.7 \mu \mathrm{~F}, \mathrm{C}_{\mathrm{O}}=22 \mu \mathrm{~F}$

Figure 20. Inhibit transient


## 6 Typical application

Figure 21. Application circuits


Figure 22. Application circuits


## $7 \quad$ Application information

The ST1S09 is an adjustable current mode PWM step-down DC-DC converter with internal 2 A power switch, packaged in a DFN6 $3 \times 3 \mathrm{~mm}$.

The device is a complete 2 A switching regulator with its internal compensation eliminating the need for additional components.

The constant frequency, current mode, PWM architecture and stable operation with ceramic capacitors results in low, predictable output ripple.

The over-voltage protection circuit acts when the output voltage is over $10 \%$ of the rated voltage and within 200 ns the low side MOSFET will be turned on to clamp the output transient. The current limit for clamping is about 400 mA . When the output voltage drops to about 5 \% above the nominal level, the device returns to nominal closed loop switching operation.

The open drain Power Good (PG) pin is released when the output voltage is higher than $0.92 \times \mathrm{V}_{\mathrm{O}} \mathrm{NOM}$. If the output voltage is below $0.92 \times \mathrm{V}_{\mathrm{O}}$, the PG pin goes to low impedance.
Other circuits fitted to the device protection are the thermal shut-down block, which turns off the regulator when the junction temperature exceeds $150^{\circ} \mathrm{C}$ (typ), and the cycle-by-cycle current limiting, which provides protection against shorted outputs.

As an adjustable regulator, the ST1S09's output voltage is determined by an external resistor divider. The desired value is given by the following equation:

## Equation 1

$\mathrm{V}_{\mathrm{O}}=\mathrm{V}_{\mathrm{FB}}\left[1+\mathrm{R}_{1} / \mathrm{R}_{2}\right]$
To utilize the device, only a few components are required: an inductor, two capacitors and the resistor divider. The inductor chosen must be able to reach peak current level without saturating. Its value can be selected while taking into account that a large inductor value increases the efficiency at low output current and reduces output voltage ripple, while a smaller inductor can be chosen when it is important to reduce package size and the total cost of the application. Finally, the ST1S09 has been designed to work properly with X5R or X7R SMD ceramic capacitors both at the input and at the output. These types of capacitors, due to their very low series resistance (ESR), minimize the output voltage ripple. Other low ESR capacitors can be used according to the need of the application without compromising the correct functioning of the device.

## 8 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK ${ }^{\circledR}$ packages, depending on their level of environmental compliance. ECOPACK ${ }^{\circledR}$ specifications, grade definitions and product status are available at: www.st.com. ECOPACK ${ }^{\circledR}$ is an ST trademark.

DFN6D (3x3) Mechanical Data

| Dim. | mm. |  |  | inch. |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 0.80 |  | 1.00 | 0.031 |  | 0.039 |
| A1 | 0 | 0.02 | 0.05 | 0 | 0.001 | 0.002 |
| A3 |  | 0.20 |  |  | 0.008 |  |
| b | 0.23 |  | 0.45 | 0.009 |  | 0.018 |
| D | 2.90 | 3.00 | 3.10 | 0.114 | 0.118 | 0.122 |
| D2 | 2.23 |  | 2.50 | 0.088 |  | 0.098 |
| E | 2.90 | 3.00 | 3.10 | 0.114 | 0.118 | 0.122 |
| E2 | 1.50 |  | 1.75 | 0.059 |  | 0.069 |
| e |  | 0.95 |  |  | 0.037 |  |
| L | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 |



Figure 23. DFN6 ( $3 \times 3 \mathrm{~mm}$ ) footprint recommended data


Tape \& Reel QFNxx/DFNxx (3x3) Mechanical Data

| Dim. | mm. |  |  | inch. |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A |  |  | 330 |  |  | 12.992 |
| C | 12.8 |  | 13.2 | 0.504 |  | 0.519 |
| D | 20.2 |  |  | 0.795 |  |  |
| N | 60 |  |  | 2.362 |  |  |
| T |  | 3.3 |  |  | 0.130 |  |
| Ao |  | 3.3 |  |  | 0.130 |  |
| Bo |  | 1.1 |  |  | 0.043 |  |
| Ko |  | 4 |  |  | 0.157 |  |
| Po |  | 8 |  |  | 0.315 |  |
| P |  |  |  |  |  |  |



## $9 \quad$ Revision history

Table 8. Document revision history

| Date | Revision | Changes |
| :---: | :---: | :--- |
| 18-Jun-2007 | 1 | First release. |
| 05-Jul-2007 | 2 | Removed incorrect watermark. |
| 31-Jan-2008 | 3 | Modified: Table 6 on page 6. |
| 19-Apr-2010 | 4 | Modified: Table 1 on page 1. |

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[^0]:    1. Available on request.
[^1]:    1. Guaranteed by design, but not tested in production.
